WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a wiring layer having a plurality of divided wirings extending in a predetermined direction, the plurality of divided wirings being divided from each other in a direction perpendicular to the extending direction, the wiring layer being formed of a plurality of grains, the divided wirings each having a width smaller than a size of the grains forming the wiring layer, the wiring layer being formed on a semiconductor substrate; and

a plurality of slit-shaped non-wiring layers, each of which is formed between the plurality of divided wirings of the wiring layer, the non-wiring layers extending in the extending direction of the plurality of the divided wirings.

2. A semiconductor device according to claim 1, the wiring layer having a width which is greater than the size of the grains forming the wiring layer.

3. A semiconductor device according to claim 1, the wiring layer having a width which is greater than a minimum wiring width prescribed by design rules.

4. A semiconductor device according to claim 1, the wiring layer being formed of an alloy mainly containing aluminum.

5. A semiconductor device according to claim 1, the non-wiring layers including an insulating film.

6. A semiconductor device according to claim 1, the width of each of the divided wirings being shorter than 1.5 μm.

7. A semiconductor device comprising:

a first insulating film formed on a semiconductor substrate;

a wiring layer having a plurality of divided wirings extending in a first direction, the wiring layer being formed of a plurality of grains and formed on the first insulating film; and

a plurality of slit-shaped second insulating films formed at predetermined intervals in a second direction perpendicular to the first direction, each of the plurality of second insulating films being arranged between the plurality of divided wirings of the wiring layer, and extending in the first direction,

wherein each of the plurality of the divided wirings has a width smaller than a size of the grains forming the wiring layer.

8. A semiconductor device according to claim 7, the wiring layer having a width which is greater than the size of the grains forming the wiring layer.

9. A semiconductor device according to claim 7, the wiring layer having a width which is greater than a minimum wiring width prescribed by design rules.

10. A semiconductor device according to claim 7, the wiring layer being formed of an alloy mainly

containing aluminum.

11. A semiconductor device according to claim 7, the width of each of the divided wirings being shorter than 1.5 μm.